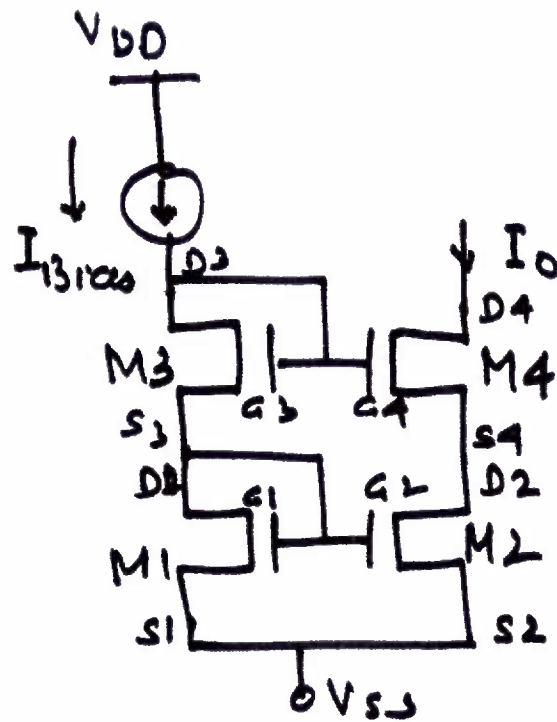


CASCODE CURRENT MIRROR



CDEEP
IIT Bombay

EE 618 L 14 / Slide 1



M2 & M4 form Cascode Stage leading to Higher Rout.

However we must ensure that M2 & M4 are in Saturation. In current source case, not only we need High Rout, but very small V_{min}

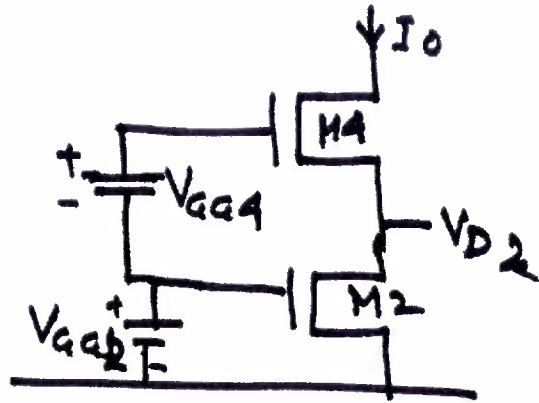
For a 5μ ($V_{DD} = 5V$) Process

$$V_{Th} \approx 0.83V \quad \& \quad V_{OV} = 0.37V$$

$$\text{i.e. } V_{GS} = 1.2V$$

V_{min} is drop across current source





If $V_{GS} = 1.2 \text{ V}$

then $V_{GS1} = V_{GS2} = 1.2$

and $V_{GS3} = V_{GS4} = 1.2 + 1.2$
 $= 2.4 \text{ V}$

For M4 in Saturation

$$V_{DS4} > V_{GS4} - V_T$$

$$\text{Now } V_{D2} = V_{S4}$$

For M2 to saturate $V_{DS2} \geq V_{GS2} - V_T$

If we keep $V_{DS2} = V_{GS2}$, then M2 is always in Saturation

$$\therefore V_{DS2} = V_{GS1} = V_{GS2} = 1.2 \text{ V}$$

For M4 to be in saturation $V_{D4} - V_{D2} \geq V_{GS4} - V_{D2} - V_T$

$$\text{or } V_{D4} \geq 2.4 - 0.83 = 1.57 \text{ V} = (2V_{OV} + V_T)$$

$$\text{i.e. } V_{min} \geq 2V_{OV} + V_T$$

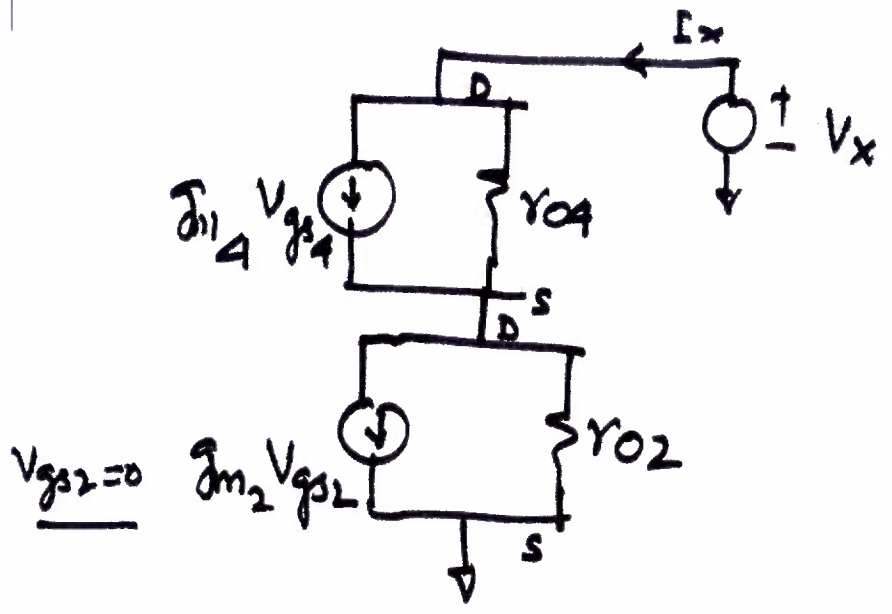


CDEEP
IIT Bombay

EE 618 L 14 / Slide 2



ROUT evaluation

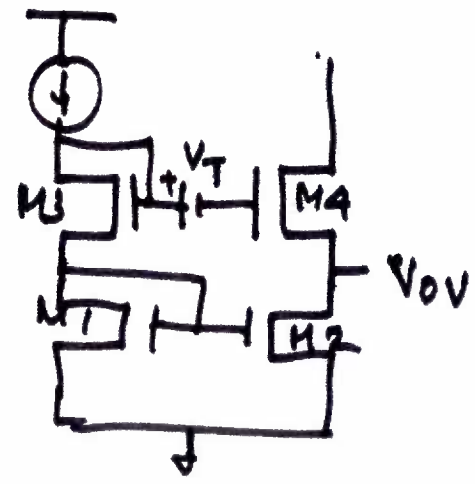


$$\begin{aligned}
 R_{out} &= r_{o4} (1 + g_{m2} r_{o2}) + r_{o2} \\
 &\approx r_{o4} (1 + g_{m2} r_{o2}) \\
 &\approx g_{m4} r_{o2} r_{o4} \text{ (Cascode Effect)}
 \end{aligned}$$

To reduce V_{min} , we use additional Battery of V_T between Gates of $M3$ & $M4$.

This gives $V_{G4} = 2V_{ov} + V_T$

$$\begin{aligned}
 \therefore V_{min} &= 2V_{ov} + V_T - (V_{ov} + V_T) \\
 &= V_{ov}
 \end{aligned}$$



Sensitivity Analysis

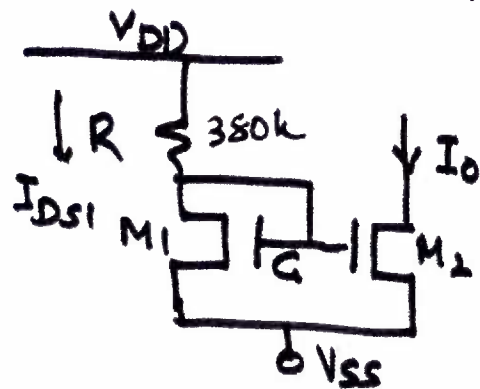
$$S_x^y = \lim_{\Delta x \rightarrow 0} \frac{\Delta y / y}{\Delta x / x} \quad \text{Definition}$$



CDEEP
IIT Bombay

EE 618 L 14 / Slide 4

(i) Sensitivity of Current Source wrt V_{DD}
in a Simple Current Mirror (W/L are equal for M_1 & M_2)



We have $I_O = I_{DS1} = 10 \mu A$

However $I_{DS1} = \frac{V_{DD} - V_{SS} - V_{GS}}{R}$

We need to find $S_{V_{DD}}^{I_O} = \lim_{\Delta V_{DD} \rightarrow 0} \frac{\Delta I_O / I_O}{\Delta V_{DD} / V_{DD}}$

$$\text{or } S_{V_{DD}}^{I_O} = \frac{V_{DD}}{I_O} \frac{\partial I_O}{\partial V_{DD}}$$

$$\text{But } \frac{\partial I_O}{\partial V_{DD}} = \frac{\partial I_{DS1}}{\partial V_{DD}} = \frac{1}{R}$$

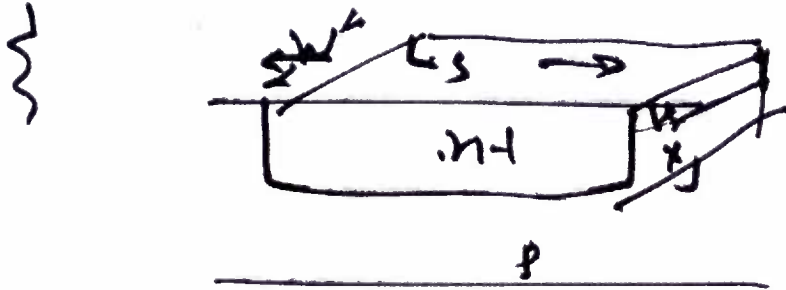
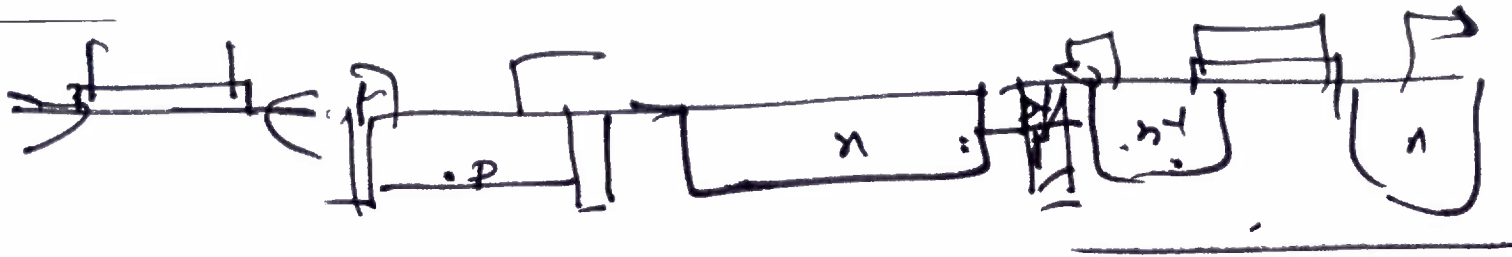
$$\therefore S_{V_{DD}}^{I_O} = \frac{V_{DD}}{I_O R} = \frac{2.5}{10^{-5} \times 380k} \approx 0.66$$

$$\Delta \frac{\Delta I_O}{I_O} = \frac{0.66 \times 0.2}{2.5} \quad (\text{if } V_{DD} \text{ becomes } V_{DD} \pm 0.1V) \approx 5\%$$

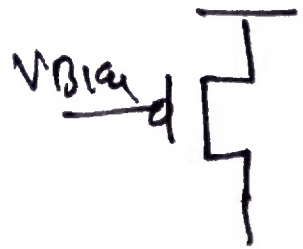


CDEEP
IIT Bombay

EE 618 L 14 / Slide 5



$$R_c = R_s \cdot \frac{L}{w}$$



$$G = q \mu_n n t$$

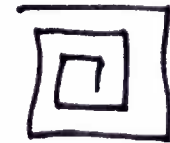
$$R = \frac{\rho \cdot l \cdot t}{A}$$

$$A = w \cdot L_s$$

$$t = x_j$$

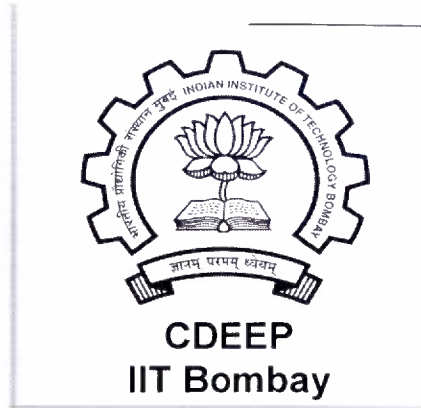
$$R = \frac{1}{q \mu_n n t}$$

$$R_s = \frac{\rho}{t}$$



$$1. \quad TC_f(R) = \frac{1}{R} \frac{dR}{dT} \approx +2000 \text{ ppm}/^\circ\text{C}$$

Where R is created from Diffused nt region



EE 618 L 4 / Slide 6

$$2. \quad TC_f(V_T) = -3000 \text{ ppm}/^\circ\text{C} \quad \text{for } V_T \approx 0.8\text{V}$$

$$\text{Typically } \frac{\partial V_T}{\partial T} = -2.4 \text{ mV}/^\circ\text{C}$$

$$3. \quad \text{For a MOSFET } \beta' = \mu C_{ox}, \therefore \beta'(T) = \beta'(0) \left(\frac{T}{T_0}\right)^{-3/2}$$

$$\text{This gives } \frac{1}{\beta'} \frac{\partial \beta'}{\partial T} \approx -\frac{1.5}{T}, \quad T \text{ in } ^\circ\text{K}$$

$$\begin{aligned} \text{or } TC_f(\beta') &\approx -\frac{1.5}{T} \rightarrow = \frac{1.5}{300} = \frac{1}{200} = \frac{10^6}{200} \text{ ppm}/^\circ\text{C} \\ &= 5000 \text{ ppm}/^\circ\text{C} \end{aligned}$$



CDEEP
IIT Bombay

EE 618 L 14 / Slide 7

(2) Temperature Sensitivity

$$TC_f(I_0) = \frac{1}{I_0} \frac{\partial I_0}{\partial T}$$

$$S_T^{I_0} = \lim_{\Delta T \rightarrow 0} \frac{\Delta I_0 / I_0}{\Delta T / T} = \frac{T}{I_0} \frac{\partial I_0}{\partial T} = T \cdot TC_f(I_0)$$

$TC_f(I_0) \Rightarrow$ evaluation

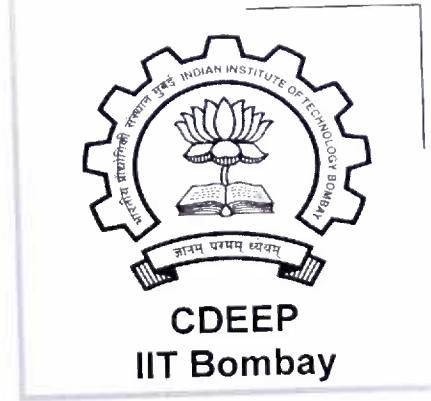
$$I_0 = I_{DS1} = \frac{V_{DD} - V_{as} - V_{ss}}{R} \quad \text{for Simple Mirror}$$

$$\frac{\partial I_0}{\partial T} = \frac{\partial I_{DS1}}{\partial T} = -\frac{1}{R} \frac{\partial V_{as}}{\partial T} + \frac{1}{R} V_{as} \frac{\partial R}{\partial T}$$

$$\therefore TC_f(I_0) = \frac{1}{I_0} \left[-\frac{1}{R} \frac{\partial V_T}{\partial T} - \frac{1}{R} \frac{\partial}{\partial T} \sqrt{\frac{2I_0 R}{\beta}} + \frac{1}{R} \frac{\partial R}{\partial T} \right]$$

Typical value

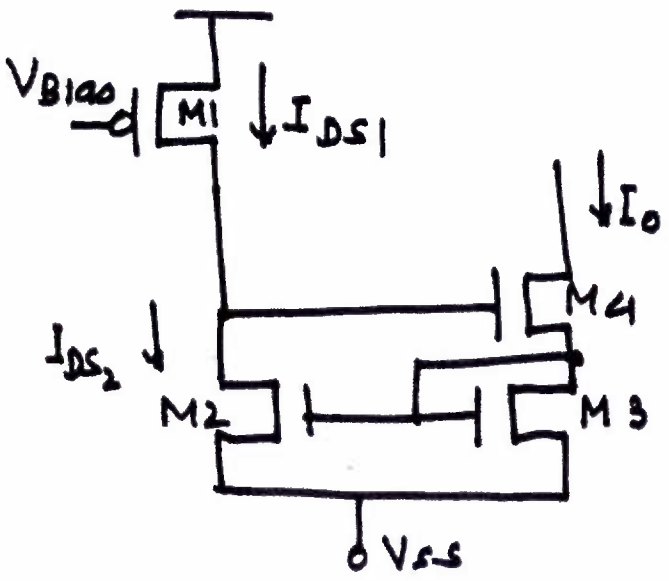
$$\begin{aligned} TC_f(I_0) &= 0.17 \% / ^\circ\text{C} = 1700 \text{ ppm}/^\circ\text{C} \\ &= 1700 \text{ ppm}/^\circ\text{C} \end{aligned}$$



Using -ve feedback, Simple Current Mirror can further be improved. Two such circuits are

- 1. Wilson Mirror
- 2. Regulated Cascode

Wilson Current Mirror:



By Using P-device with proper bias we can create stable & Reference current I_{DS1} . V_{Bias} is normally taken from a 'Stable Band Gap reference'

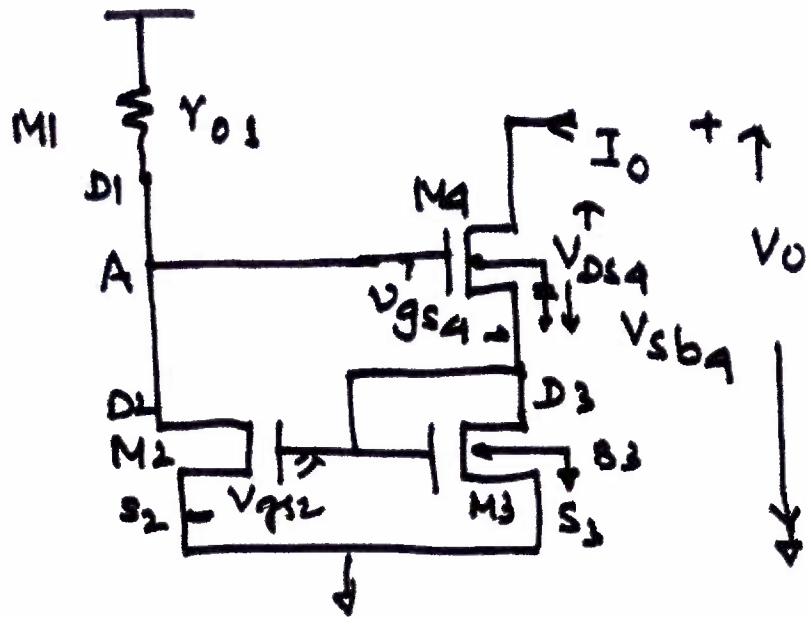
This Current Mirror has

- (i) I_O much stable than Simple Case
- (ii) Output Impedance is further improved.

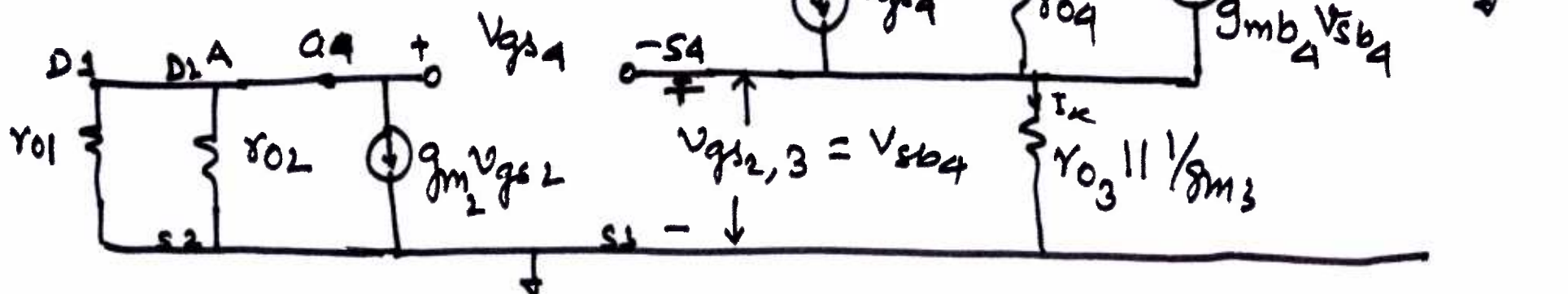


CDEEP
IIT Bombay

EE 618 L 14 / Slide 9



- V_O increases
- I_{DS4} increases
- $I_{DS4} = I_{DS3}$ & hence increase of I_{DS4} increases I_{DS2} .
- V_A decreases
- V_{GS4} decreases → I_{DS4} ↓



$$V_{sb4} = V_{gs2} = V_{gs3} = I_x (r_{O3} \parallel 1/g_{m3})$$

$$V_{gs4} = -g_{m2} V_{gs2} (r_{O1} \parallel r_{O2}) - V_{gs2}$$

$$\text{or } v_{gs4} = -[1 + g_{m2}(r_{o1} \parallel r_{o2})] v_{gs2}$$

$$= -[1 + g_{m2}(r_{o1} \parallel r_{o2})] v_{sb4}$$

$$\therefore v_{gs4} = -[1 + g_{m2}(r_{o1} \parallel r_{o2})] I_x (r_{o3} \parallel \frac{1}{g_{m3}}) \quad \text{--- (1)}$$

Further

$$I_x = g_{m4} v_{gs4} - g_{mb4} v_{sb4} + \frac{v_x - v_{gs2}}{r_{o4}} \quad \text{--- (2)}$$

From (1) & (2)

$$R_{out} = \frac{v_x}{I_x} = r_{o4} [1 + g_{m4}(r_{o3} \parallel \frac{1}{g_{m3}})] (1 + g_{m2}(r_{o1} \parallel r_{o2}))$$

$$+ g_{mb4} [(r_{o3} \parallel \frac{1}{g_{m3}}) + \frac{1}{r_{o4}} (r_{o3} \parallel \frac{1}{g_{m3}}) r_o]$$



CDEEP
IIT Bombay

EE 618 L 14 / Slide 10